

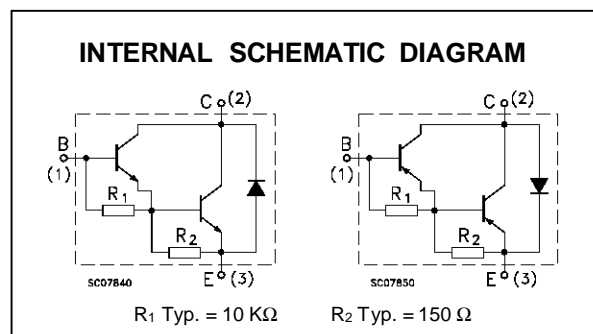
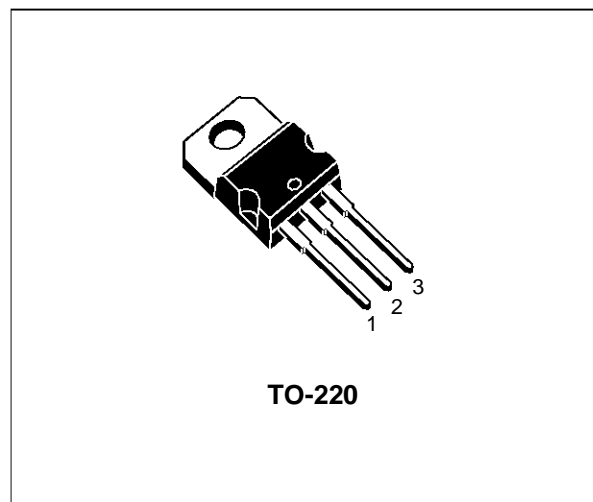
**COMPLEMENTARY SILICON POWER
DARLINGTON TRANSISTORS**

- BDX53B, BDX53C, BDX54B AND BDX54C ARE SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The BDX53A, BDX53B and BDX53C are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration and are mounted in Jedec TO-220 plastic package. They are intended for use in hammer drivers, audio amplifiers and other medium power linear and switching applications.

The complementary PNP types are the BDX54A, BDX54B and BDX54C respectively.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit	
		NPN	BDX53A	BDX53B		BDX53C
		PNP	BDX54A	BDX54B		BDX54C
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	60	80	100	V	
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	60	80	100	V	
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	5			V	
I_C	Collector Current	8			A	
I_{CM}	Collector Peak Current (repetitive)	12			A	
I_B	Base Current	0.2			A	
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	60			W	
T_{stg}	Storage Temperature	-65 to 150			$^\circ C$	
T_j	Max. Operating Junction Temperature	150			$^\circ C$	

BDX53A/53B/53C-BDX54A/54B/54C

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	2.08	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	70	°C/W

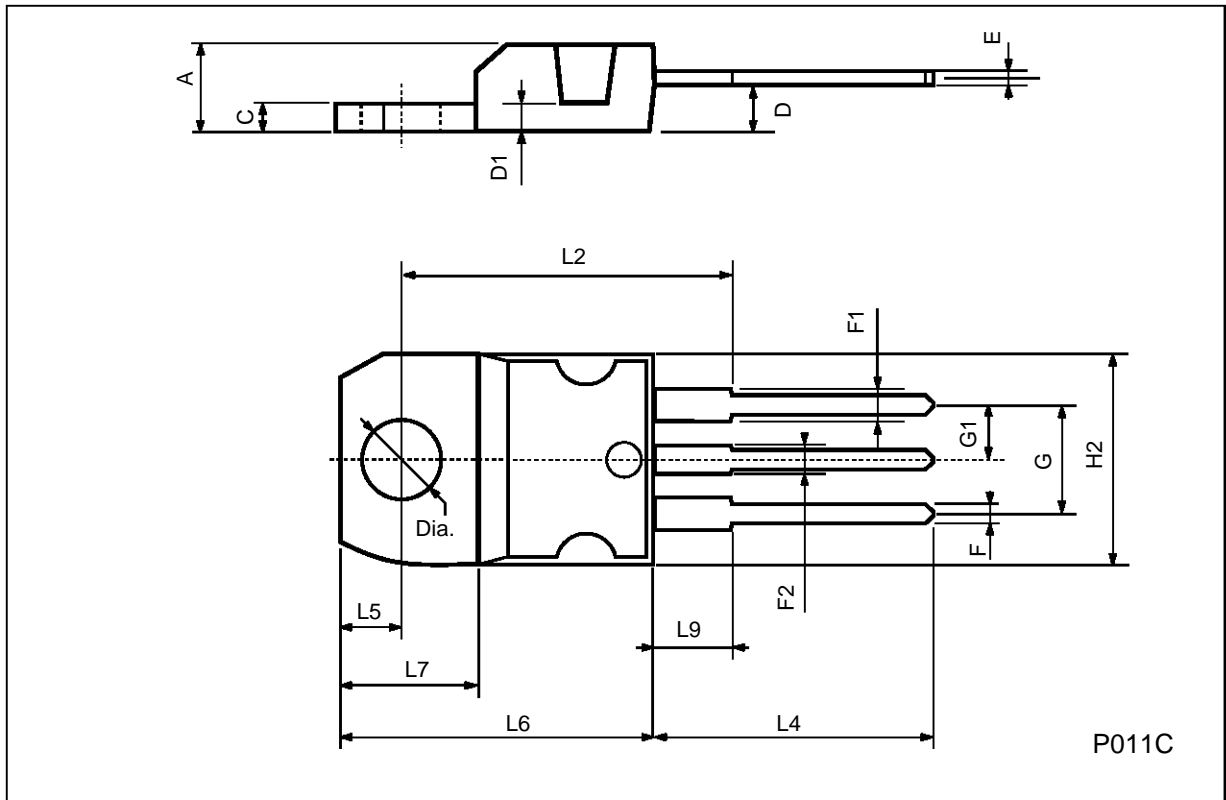
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	for BDX53A/54A V _{CB} = 60 V for BDX53B/54B V _{CB} = 80 V for BDX53C/54C V _{CB} = 100V			0.2 0.2 0.2	mA mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for BDX53A/54A V _{CB} = 30 V for BDX53B/54B V _{CB} = 40 V for BDX53C/54C V _{CB} = 50V			0.5 0.5 0.5	mA mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA for BDX53A/54A for BDX53B/53B for BDX53C/54C	60 80 100			V V V
V _{CE(sat)*}	Collector-emitter Saturation Voltage	I _C = 3 A I _B = 12 mA			2	V
V _{BE(sat)*}	Base-emitter Saturation Voltage	I _C = 3 A I _B = 12 mA			2.5	V
h _{FE*}	DC Current Gain	I _C = 3 A V _{CE} = 3 V	750			
V _{F*}	Parallel-diode Forward Voltage	I _F = 3 A I _F = 8 A		1.8 2.5	2.5	V V

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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